

QUADRUPLE BILATERAL SWITCHES

The HEF4016B has four independent analogue switches (transmission gates). Each switch has two input/output terminals (Y/Z) and an active HIGH enable input (E). When E is connected to V_{DD} a low impedance bidirectional path between Y and Z is established (ON condition). When E is connected to V_{SS} the switch is disabled and a high impedance between Y and Z is established (OFF condition). Current through a switch will not cause additional V_{DD} current provided the voltage at the terminals of the switch is maintained within the supply voltage range; $V_{DD} \geq (V_Y, V_Z) \geq V_{SS}$. Inputs Y and Z are electrically equivalent terminals.

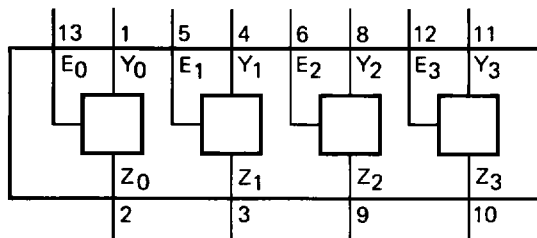


Fig. 1 Functional diagram.

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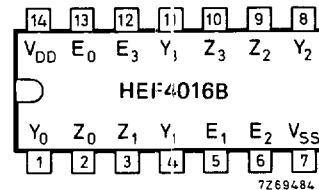


Fig. 2 Pinning diagram.

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HEF4016BP(N): 14-lead DIL; plastic (SOT27-1)
 HEF4016BD(F): 14-lead DIL; ceramic (cerdip) (SOT73)
 HEF4016BT(D): 14-lead SO; plastic (SOT108-1)
 (): Package Designator North America

PINNING

E_0 to E_3 enable inputs

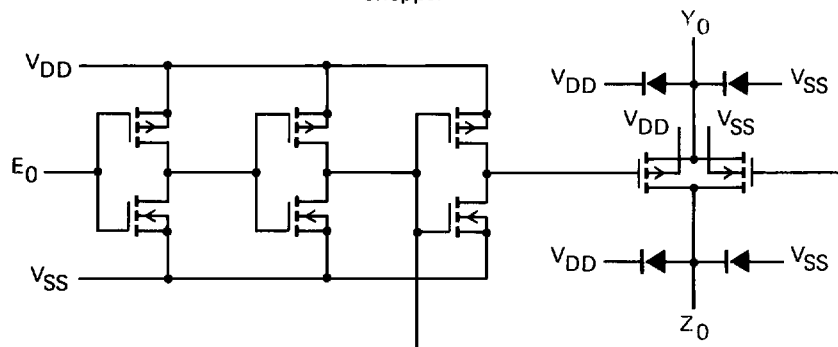
Y_0 to Y_3 input/output terminals

Z_0 to Z_3 input/output terminals

APPLICATION INFORMATION

Some examples of applications for the HEF4016B are:

- Signal gating
- Modulation
- Demodulation
- Chopper



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Fig. 3 Schematic diagram (one switch).

HEF4016B

gates

RATINGS

Limiting values in accordance with the Absolute Maximum System (IEC 134)

Power dissipation per sw tch

P max. 100 mW

For other RATINGS see Family Specifications

D.C. CHARACTERISTICS

T_{amb} = 25 °C; V_{SS} = 0 V (unless otherwise specified)

parameter	V _{DD} V	symbol	typ.	max.	unit	conditions
ON resistance	5	R _{ON}	8000	—	Ω	E _n at V _{IH} V _{is} = 0 to V _{DD} see Fig. 4
	10		230	690	Ω	
	15		115	350	Ω	
ON resistance	5	R _{ON}	140	425	Ω	E _n at V _{IH} V _{is} = V _{SS} see Fig. 4
	10		65	195	Ω	
	15		50	145	Ω	
ON resistance	5	R _{ON}	170	515	Ω	E _n at V _{IH} V _{is} = V _{DD} see Fig. 4
	10		95	285	Ω	
	15		75	220	Ω	
'Δ' ON resistance between any two channels	5	ΔR _{ON}	200	—	Ω	E _n at V _{IH} V _{is} = 0 to V _{DD} see Fig. 4
	10		15	—	Ω	
	15		10	—	Ω	

parameter	V _{DD} V	symbol	T _{amb} (°C)			unit	condition			
			—40 min.	+25 max.	+85 min. max.					
Quiescent device current	5	I _{DD}	—	1,0	—	7,5	μA V _{SS} = 0; all valid input combinations; V _I = V _{SS} or V _{DD}			
	10		—	2,0	—	15,0				
	15		—	4,0	—	30,0				
Input leakage current at E _n	15	± I _{IN}	—	—	—	300	—	1000	nA	E _n at V _{SS} or V _{DD}
OFF-state leakage current, any channel OFF	5	I _{OZ}	—	—	—	—	—	—	nA	E _n at V _{IL} ; V _{is} = V _{SS} or V _{DD} ; V _{os} = V _{DD} or V _{SS}
	10		—	—	—	—	—	—	nA	
	15		—	—	—	200	—	—	nA	
E _n input voltage LOW	5	V _{IL}	—	1,5	—	1,5	—	1,5	V	switch OFF; see Fig. 9 for I _{OZ}
	10		—	3,0	—	3,0	—	3,0	V	
	15		—	4,0	—	4,0	—	4,0	V	
E _n input voltage HIGH	5	V _{IH}	3,5	—	3,5	—	3,5	—	V	low-impedance between Y and Z (ON condition) see R _{ON} switch
	10		7,0	—	7,0	—	7,0	—	V	
	15		11,0	—	11,0	—	11,0	—	V	

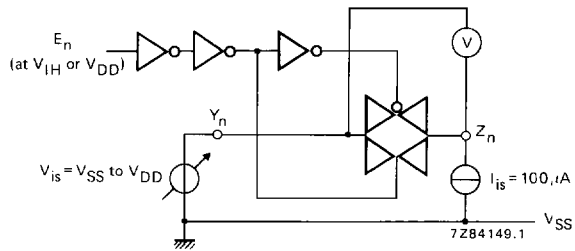


Fig. 4 Test set-up for measuring R_{ON} .

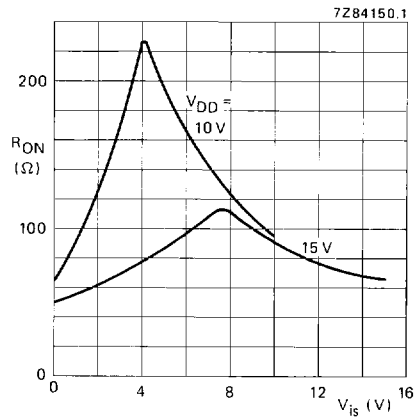


Fig. 5 Typical R_{ON} as a function of input voltage.

$E_n > V_{IH}$
 $I_{is} = 100 \mu A$
 $V_{SS} = 0 V$

A.C. CHARACTERISTICS $V_{SS} = 0\text{ V}$; $T_{amb} = 25\text{ }^{\circ}\text{C}$; input transition times $\leq 20\text{ ns}$

	V_{DD} V	symbol	typ.	max.			
Propagation delays $V_{is} \rightarrow V_{os}$ HIGH to LOW	5	tPHL	25	50	ns	} note 1	
	10		10	20	ns		
	15		5	10	ns		
	LOW to HIGH	5	tPLH	20	40	ns	} note 1
		10		10	20	ns	
		15		5	10	ns	
Output disable times $E_n \rightarrow V_{os}$ HIGH	5	tPHZ	90	130	ns	} note 2	
	10		80	110	ns		
	15		75	100	ns		
	LOW	5	tPLZ	85	120	ns	} note 2
		10		75	100	ns	
		15		75	100	ns	
Output enable times $E_n \rightarrow V_{os}$ HIGH	5	tPZH	40	80	ns	} note 2	
	10		20	40	ns		
	15		15	30	ns		
	LOW	5	tPZL	40	80	ns	} note 2
		10		20	40	ns	
		15		15	30	ns	
Distortion, sine-wave response	5		—		%	} note 3	
	10		0,08		%		
	15		0,04		%		
Crosstalk between any two channels	5		—		MHz	} note 4	
	10		1		MHz		
	15		—		MHz		
Crosstalk; enable input to output	5		—		mV	} note 5	
	10		50		mV		
	15		—		mV		
OFF-state feed-through	5		—		MHz	} note 6	
	10		1		MHz		
	15		—		MHz		
ON-state frequency response	5		—		MHz	} note 7	
	10		90		MHz		
	15		—		MHz		
Dynamic power dissipation per package (P)*	V_{DD} V	typical formula for P (μW)			where		
	5	$550 f_i + \Sigma(f_o C_L) \times V_{DD}^2$			f_i = input freq. (MHz)		
	10	$2\,600 f_i + \Sigma(f_o C_L) \times V_{DD}^2$			f_o = output freq. (MHz)		
15	$6\,500 f_i + \Sigma(f_o C_L) \times V_{DD}^2$			C_L = load capacitance (pF)			
					$\Sigma(f_o C_L)$ = sum of outputs		
					V_{DD} = supply voltage (V)		

* All enable inputs switching.

NOTES

V_{is} is the input voltage at a Y or Z terminal, whichever is assigned as input.

V_{os} is the output voltage at a Y or Z terminal, whichever is assigned as output

1. $R_L = 10\text{ k}\Omega$ to V_{SS} ; $C_L = 50\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$; $V_{is} = V_{DD}$ (square-wave); see Figs 6 and 10.

2. $R_L = 10\text{ k}\Omega$; $C_L = 50\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave);

$V_{is} = V_{DD}$ and R_L to V_{SS} for t_{PHZ} and t_{PZH} ;

$V_{is} = V_{SS}$ and R_L to V_{DD} for t_{PLZ} and t_{PZL} ; see Figs 6 and 11.

3. $R_L = 10\text{ k}\Omega$; $C_L = 15\text{ pF}$; $E_n = V_{DD}$; $V_{is} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$f_{is} = 1\text{ kHz}$; see Fig. 7.

4. $R_L = 1\text{ k}\Omega$; $V_{is} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$20 \log \frac{V_{os(B)}}{V_{is(A)}} = -50\text{ dB}$; $E_n(A) = V_{SS}$; $E_n(B) = V_{DD}$; see Fig. 8.

5. $R_L = 10\text{ k}\Omega$ to V_{SS} ; $C_L = 15\text{ pF}$ to V_{SS} ; $E_n = V_{DD}$ (square-wave); crosstalk is $|V_{os}|$ (peak value); see Fig. 6.

6. $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; $E_n = V_{SS}$; $V_{is} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$20 \log \frac{V_{os}}{V_{is}} = -50\text{ dB}$; see Fig. 7.

7. $R_L = 1\text{ k}\Omega$; $C_L = 5\text{ pF}$; $E_n = V_{DD}$; $V_{is} = \frac{1}{2}V_{DD(p-p)}$ (sine-wave, symmetrical about $\frac{1}{2}V_{DD}$);

$20 \log \frac{V_{os}}{V_{is}} = -3\text{ dB}$; see Fig. 7.

HEF4016B

gates

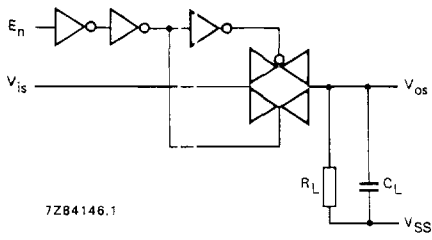


Fig. 6.

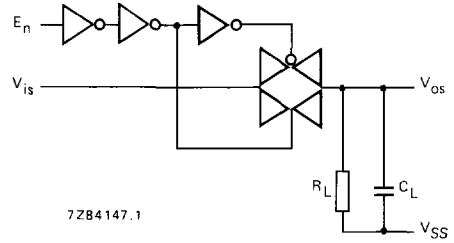
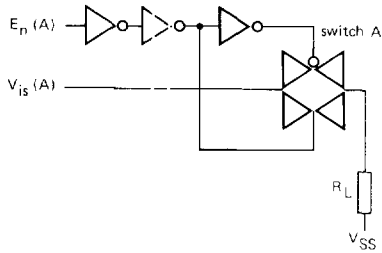
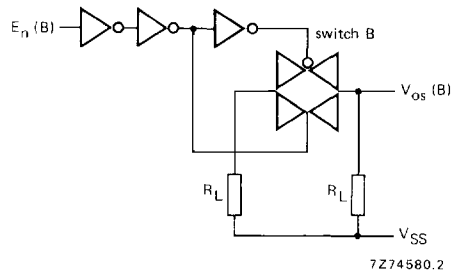


Fig. 7.



(a)



(b)

Fig. 8.

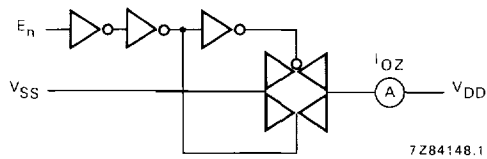


Fig. 9.

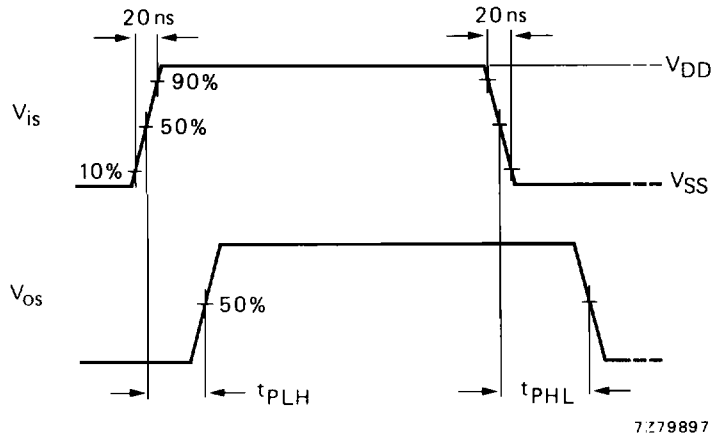
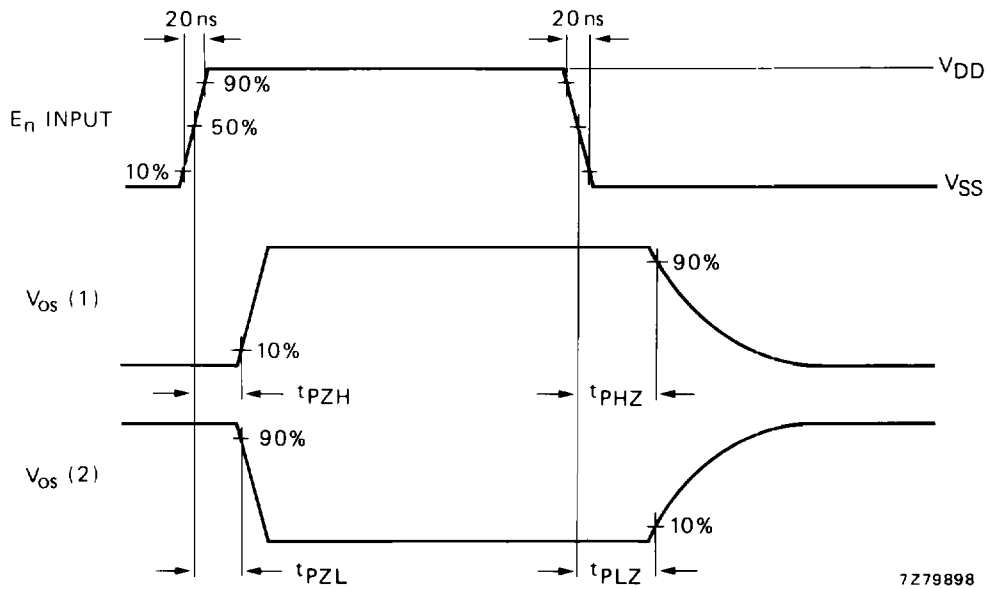


Fig. 10 Waveforms showing propagation delays from V_{is} to V_{os} .



(1) V_{is} at V_{DD} ; (2) V_{is} at V_{SS} .

Fig. 11 Waveforms showing output disable and enable times.